

Product Summary

$V_{(BR)DSS}$	$R_{DS(ON)} \text{ Max}$	$I_D \text{ Max}$ @ $T_A = +25^\circ\text{C}$
-30V	2.4Ω @ $V_{GS} = -10\text{V}$	-400mA
	4Ω @ $V_{GS} = -4.5\text{V}$	-300mA

Description

This MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

Applications

- Load Switch
- Portable Applications
- Power Management Functions

Features

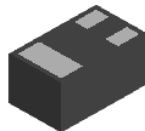
- Low On-Resistance
- Ultra-Small Surface Mount Package
- ESD Protected Gate
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Mechanical Data

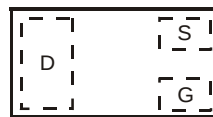
- Case: X1-DFN1006-3
- Case Material: Molded Plastic, "Green" Molding Compound.
UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish – NiPdAu over Copper Leadframe.
Solderable per MIL-STD-202, Method 208 ^(e4)
- Weight: 0.001 grams (Approximate)



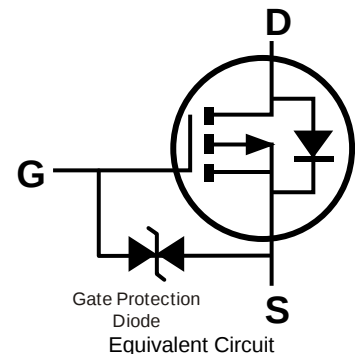
X1-DFN1006-3



Bottom View



Top View



Ordering Information (Note 4)

Part Number	Reel Size (inches)	Quantity per Reel
DMP32D5SFB-7B	7	10,000

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information



Top View
Bar Denotes Gate and Source Side

XH = Product Type Marking Code

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	-30	V
Gate-Source Voltage			V _{GSS}	±25	V
Continuous Drain Current (Note 5)	V _{GS} = -10V	T _A = +25°C T _A = +70°C	I _D	-400 -300	mA
Continuous Drain Current (Note 6)	V _{GS} = -10V	T _A = +25°C T _A = +70°C	I _D	-500 -400	mA
Pulsed Drain Current (Note 5)			I _{DM}	-1	A
Maximum Body Diode Continuous Current (Note 6)			I _S	-800	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation	(Note 5)	P _D	0.5	W
	(Note 6)		1.2	
Thermal Resistance, Junction to Ambient	(Note 5)	R _{θJA}	255	°C/W
	(Note 6)		108	
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	-30	-	-	V	V _{GS} = 0V, I _D = -1mA
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	-	-	-1	μA	V _{DS} = -30V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	-	-	±10	μA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	-1.3	-	-2.3	V	V _{DS} = V _{GS} , I _D = -250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	-	-	2.4	Ω	V _{GS} = -10V, I _D = -200mA
				4		V _{GS} = -4.5V, I _D = -200mA
Diode Forward Voltage	V _{SD}	-	0.8	1.2	V	V _{GS} = 0V, I _S = -300mA
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{ISS}	-	51	100	pF	V _{DS} = -15V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{OSS}	-	11	20	pF	
Reverse Transfer Capacitance	C _{RSS}	-	9	20	pF	
Total Gate Charge	Q _g	-	0.62	2	nC	V _{GS} = -4.5V
Total Gate Charge	Q _g	-	1.25	4	nC	V _{GS} = -10V, V _{DS} = -10V, I _D = -200mA
Gate-Source Charge	Q _{gs}	-	0.16	0.5	nC	
Gate-Drain Charge	Q _{gd}	-	0.21	0.5	nC	
Turn-On Delay Time	t _{D(ON)}	-	4.3	10	ns	V _{DS} = -15V, I _D = -500mA V _{GS} = -10V, R _G = 1Ω
Turn-On Rise Time	t _r	-	7.7	15	ns	
Turn-Off Delay Time	t _{D(OFF)}	-	31.9	60	ns	
Turn-Off Fall Time	t _f	-	17.8	40	ns	

- Notes:
5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
 6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper pad layout.
 7. Short duration pulse test used to minimize self-heating effect.
 8. Guaranteed by design. Not subject to production testing.

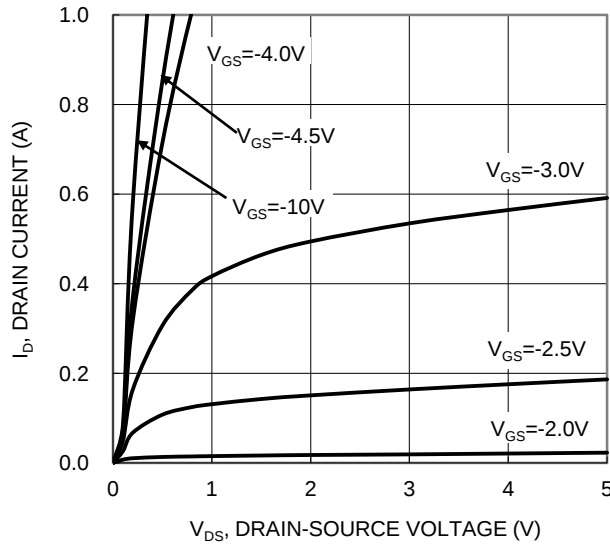


Figure 1. Typical Output Characteristic

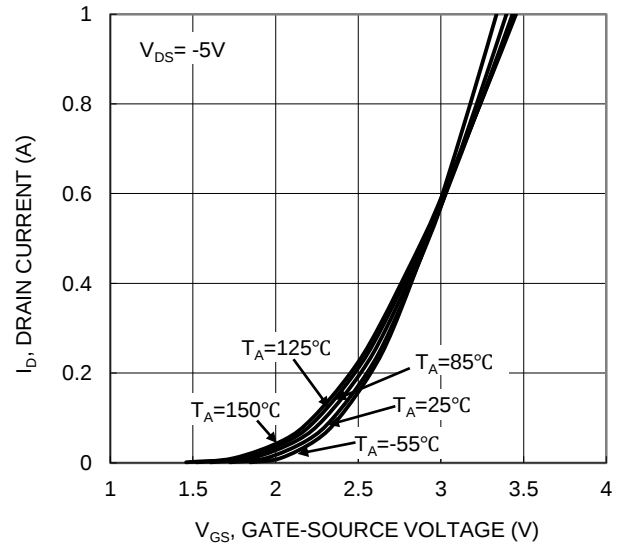


Figure 2. Typical Transfer Characteristic

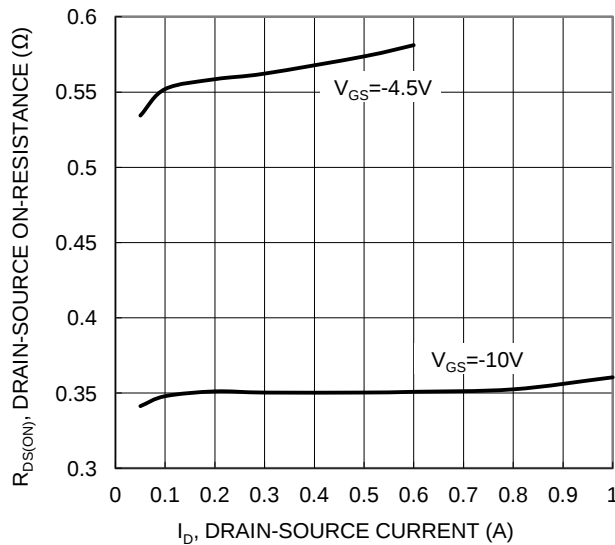


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

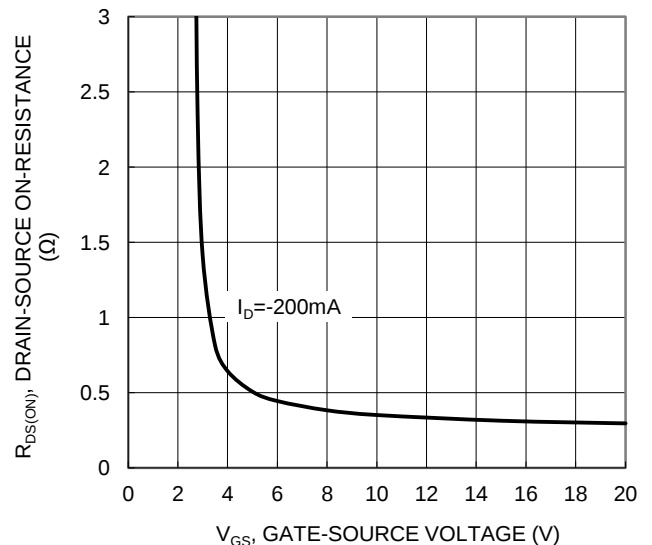


Figure 4. Typical Transfer Characteristic

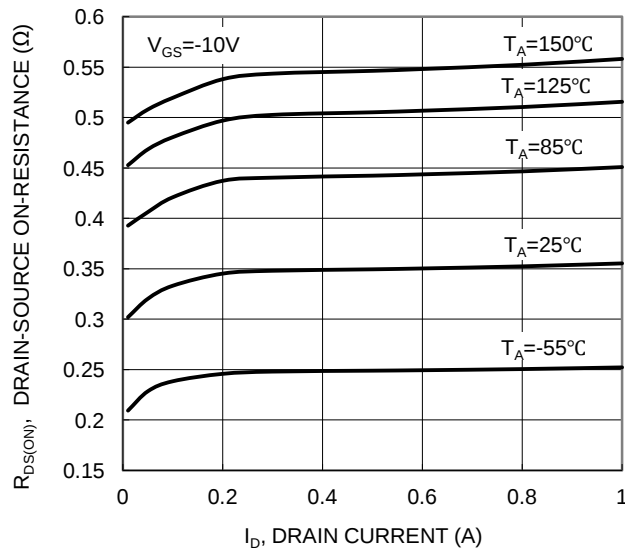


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

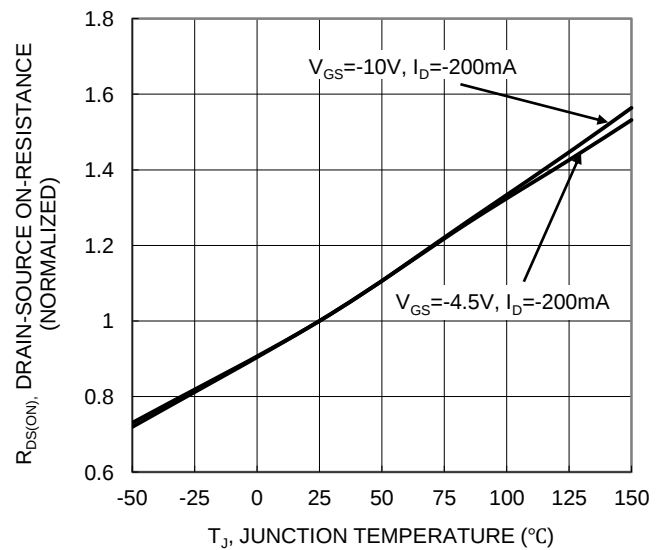
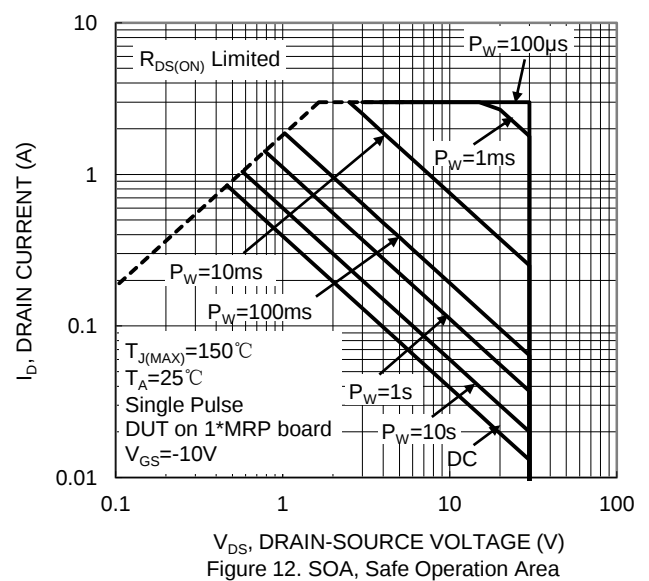
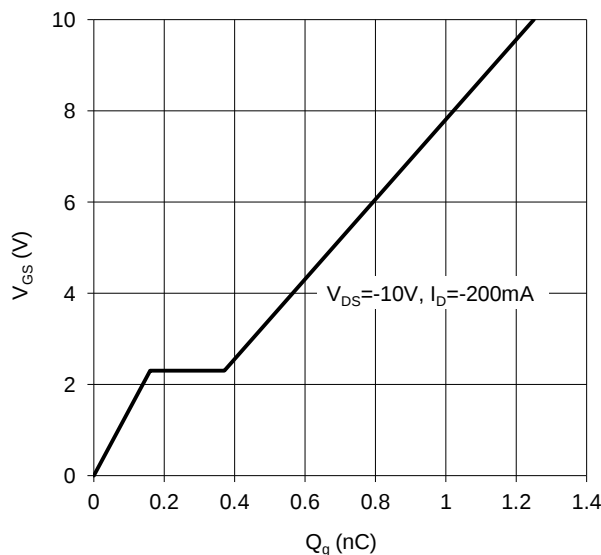
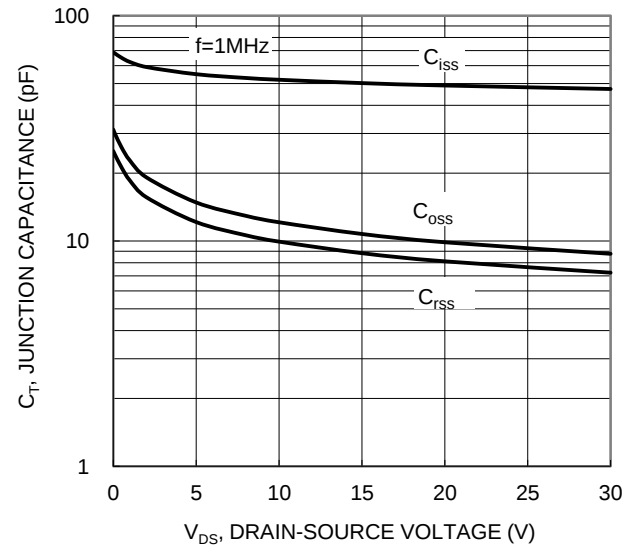
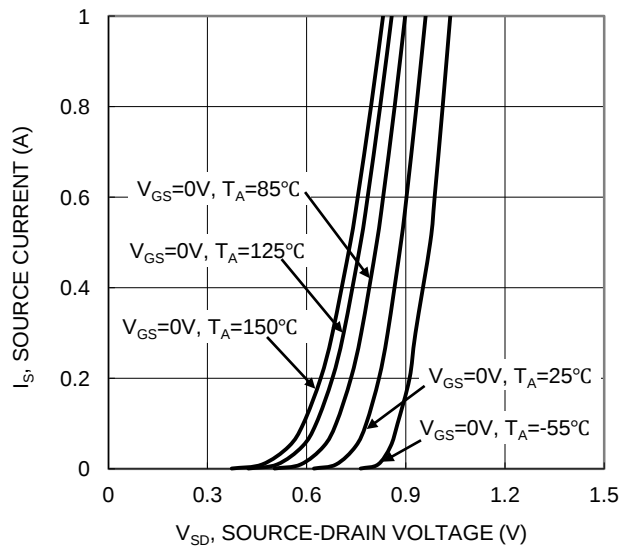
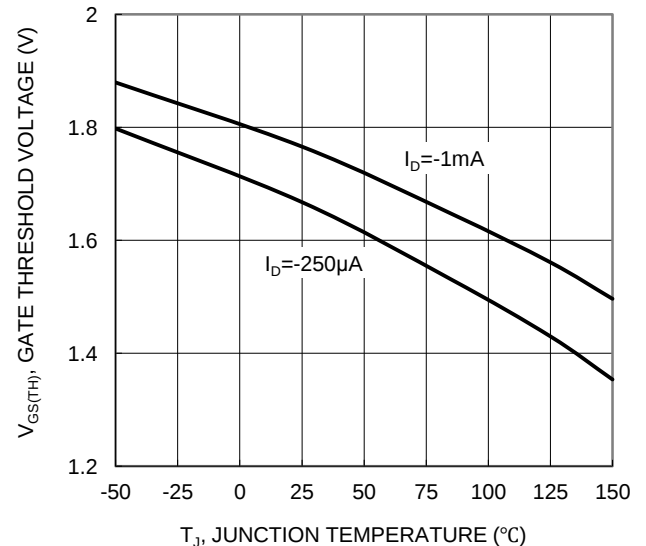
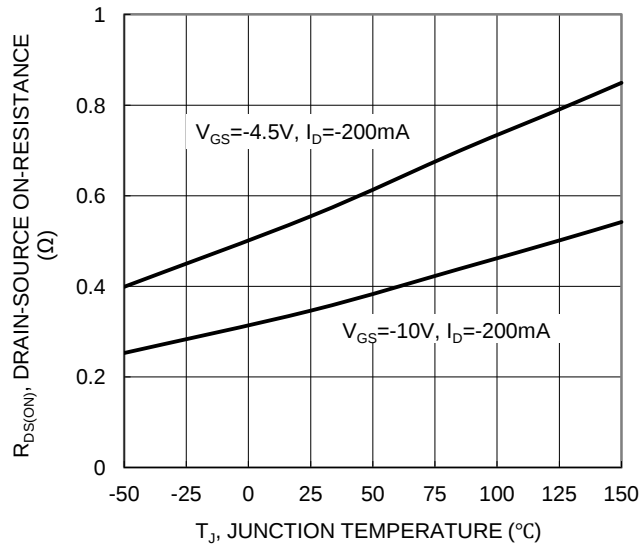
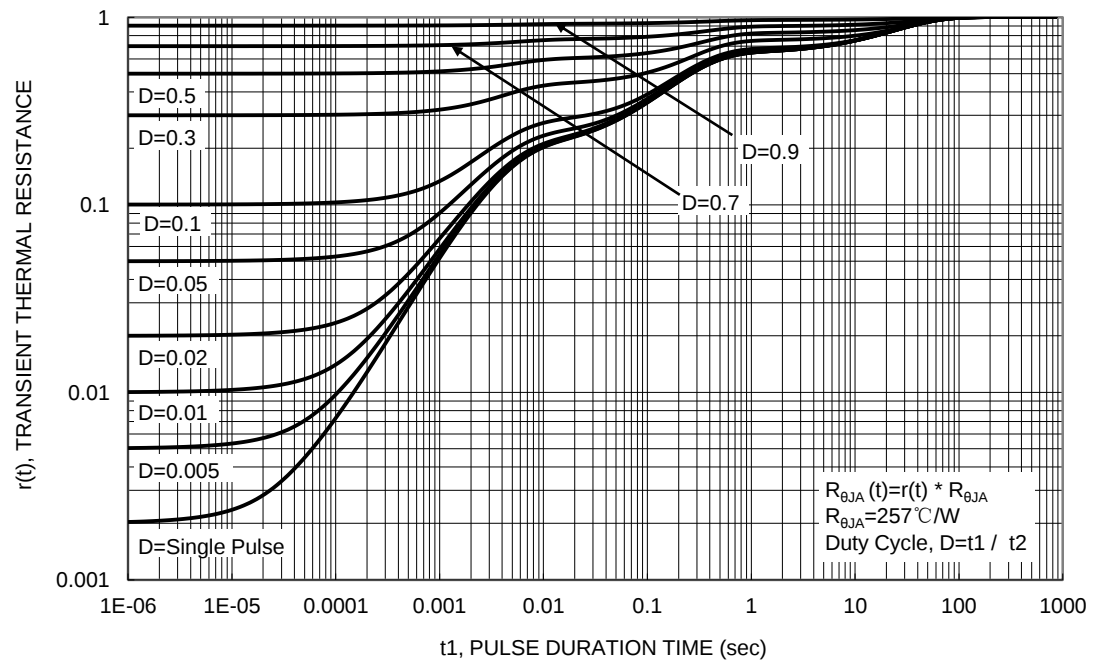


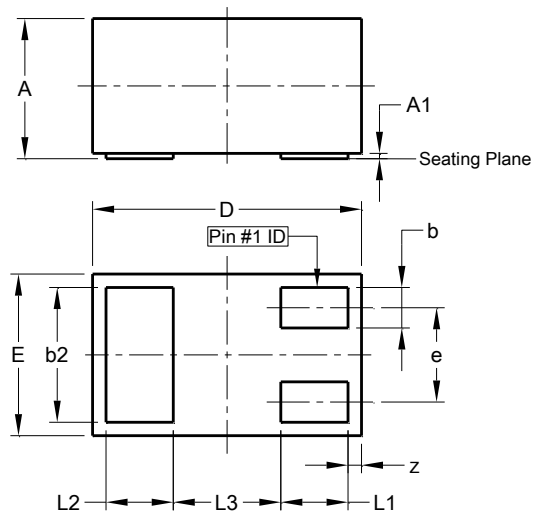
Figure 6. On-Resistance Variation with Temperature





Package Outline Dimensions

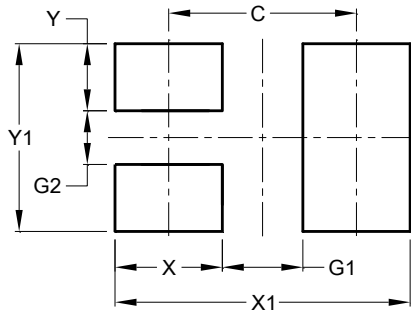
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.



X1-DFN1006-3			
Dim	Min	Max	Typ
A	0.47	0.53	0.50
A1	0.00	0.05	0.03
b	0.10	0.20	0.15
b2	0.45	0.55	0.50
D	0.95	1.075	1.00
E	0.55	0.675	0.60
e	-	-	0.35
L1	0.20	0.30	0.25
L2	0.20	0.30	0.25
L3	-	-	0.40
z	0.02	0.08	0.05
All Dimensions in mm			

Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
C	0.70
G1	0.30
G2	0.20
X	0.40
X1	1.10
Y	0.25
Y1	0.70

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